# Complementary Dual General Purpose Amplifier Transistor

# **PNP and NPN Surface Mount**



• High Voltage and High Current:  $V_{CEO} = 50 \text{ V}$ ,  $I_C = 200 \text{ mA}$ 

• High  $h_{FE}$ :  $h_{FE} = 200 \sim 400$ 

• Moisture Sensitivity Level: 1

• ESD Rating

• Human Body Model: 3A

• Machine Model: C

 S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant\*

## **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>(BR)CBO</sub>	60	Vdc
Collector–Emitter Voltage	V <sub>(BR)CEO</sub>	50	Vdc
Emitter-Base Voltage	V <sub>(BR)EBO</sub>	7.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	200	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	$P_{D}$	380	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

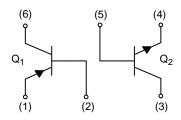


## ON Semiconductor®

www.onsemi.com



SC-74 CASE 318F STYLE 3



#### MARKING DIAGRAM



R9

= Specific Device Code

= Date Code

= Pb–Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
HN1B01FDW1T1G	SC-74 (Pb-Free)	3,000/Tape & Reel
SHN1B01FDW1T1G	SC-74 (Pb-Free)	3,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Q1: PNP ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-50	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10 \mu Adc, I_E = 0$ )	V <sub>(BR)</sub> CBO	-60	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	-7.0	-	Vdc
Collector–Base Cutoff Current $(V_{CB} = 45 \text{ Vdc}, I_E = 0)$	I <sub>CBO</sub>	-	-0.1	μAdc
	I <sub>CEO</sub>	- - -	-0.1 -2.0 -1.0	μAdc μAdc mAdc
DC Current Gain (Note 1) (V <sub>CE</sub> = 6.0 Vdc, I <sub>C</sub> = 2.0 mAdc)	h <sub>FE</sub>	-200	-400	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)	V <sub>CE(sat)</sub>	_	-0.3	Vdc

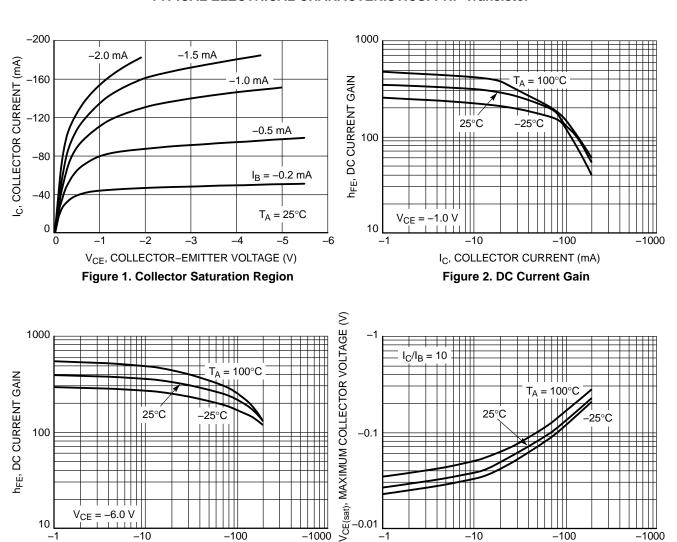
## Q2: NPN

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10 \mu Adc, I_E = 0$ )	V <sub>(BR)CBO</sub>	60	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	7.0	-	Vdc
Collector–Base Cutoff Current $(V_{CB} = 45 \text{ Vdc}, I_E = 0)$	Ісво	-	0.1	μAdc
Collector–Emitter Cutoff Current $(V_{CE} = 10 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 30 \text{ Vdc}, I_B = 0, T_A = 80^{\circ}\text{C})$	I <sub>CEO</sub>	- - -	0.1 2.0 1.0	μAdc μAdc mAdc
DC Current Gain (Note 1) (V <sub>CE</sub> = 6.0 Vdc, I <sub>C</sub> = 2.0 mAdc)	h <sub>FE</sub>	200	400	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)	V <sub>CE(sat)</sub>	-	0.25	Vdc

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, D.C.  $\leq$  2%.

#### **TYPICAL ELECTRICAL CHARACTERISTICS: PNP Transistor**



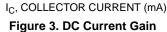


Figure 5. V<sub>BE(sat)</sub> versus I<sub>C</sub>

 $V_{CE} = -6.0 \text{ V}$ 

10

BASE-EMITTER SATURATION

VOLTAGE (V)

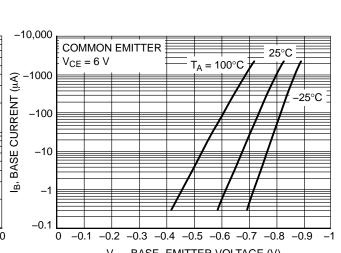


Figure 6. Base-Emitter Voltage

I<sub>C</sub>, COLLECTOR CURRENT (mA)

Figure 4. V<sub>CE(sat)</sub> versus I<sub>C</sub>

<del>-100</del>0

-10  $T_A = 25^{\circ}C$  $I_{\rm C}/I_{\rm B}=10$ -0.1 -100 -1000 IC, COLLECTOR CURRENT (mA) VBE, BASE-EMITTER VOLTAGE (V)

0.01

#### **TYPICAL ELECTRICAL CHARACTERISTICS: NPN Transistor**

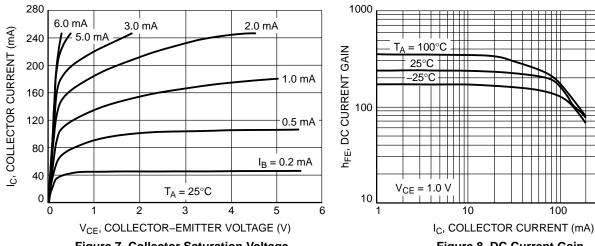
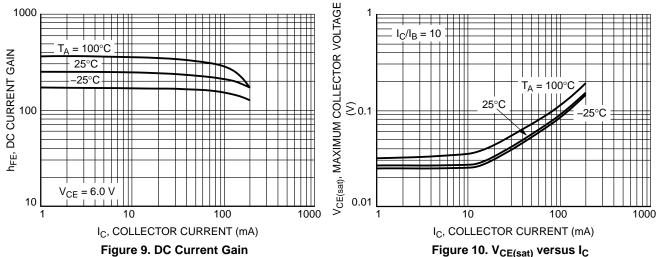


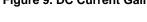
Figure 7. Collector Saturation Voltage

Figure 8. DC Current Gain

100

1000





BASE-EMITTER SATURATION

VOLTAGE (V)

10,000 10 **COMMON EMITTER** 25°C V<sub>CE</sub> = 6 V  $T_A = 100^{\circ}C$ 1000 BASE CURRENT (µA) -25°C 100 10  $T_A = 25^{\circ}C$  $I_{\rm C}/I_{\rm B}=10$ 0.1 0.1 100 1000 0.4 0.5 0.6 0.7 IC, COLLECTOR CURRENT (mA) VBE, BASE-EMITTER VOLTAGE (V)

Figure 11. V<sub>BE(sat)</sub> versus I<sub>C</sub>

Figure 12. Base-Emitter Voltage

## TYPICAL ELECTRICAL CHARACTERISTICS

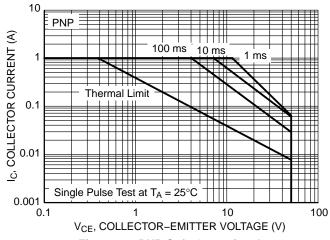


Figure 13. PNP Safe Operating Area

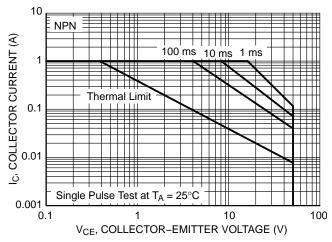
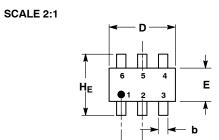


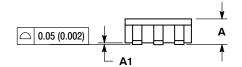
Figure 14. NPN Safe Operating Area

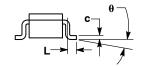


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**DATE 08 JUN 2012** 



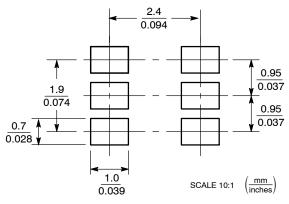




- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH
- CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 2: PIN 1. NO CONNECTION 2. COLLECTOR 3. EMITTER 4. NO CONNECTION 5. COLLECTOR 6. BASE	STYLE 3: PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	STYLE 4: PIN 1. COLLECTOR 2 2. EMITTER 1/EMITTER 2 3. COLLECTOR 1 4. EMITTER 3 5. BASE 1/BASE 2/COLLECTOR 3 6. BASE 3	STYLE 5: PIN 1. CHANNEL 1 2. ANODE 3. CHANNEL 2 4. CHANNEL 3 5. CATHODE 6. CHANNEL 4	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE

4. CATHODE 5. ANODE	4. NO CONNECTION 5. COLLECTOR	4. EMITTER 2 5. BASE 2	4. EMITTER 3 5. BASE 1/BASE 2/COLLECTOR 3	4. CHANNEL 3 5. CATHODE
6. CATHODE	6. BASE	6. COLLECTOR 1	6. BASE 3	6. CHANNEL 4
STYLE 7: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 8: PIN 1. EMITTER 1 2. BASE 2 3. COLLECTOR 2 4. EMITTER 2 5. BASE 1 6. COLLECTOR 1	STYLE 9: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 10: PIN 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 11: PIN 1. EMITTER 2. BASE 3. ANODE/CATHODE 4. ANODE 5. CATHODE 6. COLLECTOR

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